

Docket No. 202887US2

IN RE APPLICATION OF: Yuuichi HIRANO, et al.

SERIAL NO: 09/778,104

FILED: February 7, 2001

FOR: SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING SAME



ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

SIR:

Transmitted herewith is an amendment in the above-identified application.

- ☒ No additional fee is required
- ☐ Small entity status of this application under 37 C.F.R. §1.9 and §1.27 is claimed.
- ☒ Additional documents filed herewith: Marked-Up Copy, Letter Requesting Approval of Drawing Changes (marked in red) (2 Sheets), Information Disclosure Statement, PTO 1449, Cited Reference (1)

The Fee has been calculated as shown below:

CLAIMS	CLAIMS REMAINING		HIGHEST NUMBER PREVIOUSLY PAID	NO. EXTRA CLAIMS	RATE	CALCULATIONS
TOTAL	13	MINUS	20	0	x \$18 =	\$0.00
INDEPENDENT	3	MINUS	3	0	x \$84 =	\$0.00
		<input type="checkbox"/> MULTIPLE DEPENDENT CLAIMS			+ \$280 =	\$0.00
		TOTAL OF ABOVE CALCULATIONS				\$0.00
		<input type="checkbox"/> Reduction by 50% for filing by Small Entity				\$0.00
		<input type="checkbox"/> Recordation of Assignment			+ \$40 =	\$0.00
		TOTAL				\$0.00

☐ A check in the amount of **\$0.00** is attached.

☒ Please charge any additional Fees for the papers being filed herewith and for which no check is enclosed herewith, or credit any overpayment to deposit Account No. 15-0030. A duplicate copy of this sheet is enclosed.

☒ If these papers are not considered timely filed by the Patent and Trademark Office, then a petition is hereby made under 37 C.F.R. §1.136, and any additional fees required under 37 C.F.R. §1.136 for any necessary extension of time may be charged to Deposit Account No. 15-0030. A duplicate copy of this sheet is enclosed.

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13/a  
Vb  
3/4/03

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF: :  
YUUCHI HIRANO ET AL : EXAMINER: MANDALA, VICTOR A.  
SERIAL NO. : 09/778,104 :  
FILED: FEBRUARY 7, 2001 : GROUP ART UNIT: 2826  
FOR: SEMICONDUCTOR DEVICE AND:  
METHOD OF MANUFACTURING  
SAME :

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

SIR:

In response to the Office Action dated November 20, 2002, please amend the above-identified application as follows:

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TECHNOLOGY CENTER 2000

IN THE SPECIFICATION

Please amend the specification as follows:<sup>1</sup>

Please amend the paragraph on page 3, beginning at line 9, to read as shown

below:

61  
However, in accordance with the reduction of the area of the source/drain regions 104, the distance between the contact plugs 103 and the gate electrode 101 becomes smaller, so that parasitic capacitance 121 generated between the two increases, thereby raising a problem

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<sup>1</sup>The change to the specification is shown using underscoring in the attachment hereto.